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MOTOROLA
SEMICONDUCTOR TECHNICAL DATA

Order this document by MJ15023/D

PNP
MJ15023
MJ15025*

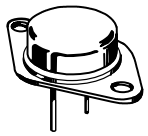
*Motorola Preferred Device

Silicon Power Transistors

The MJ15023 and MJ15025 are PowerBase power transistors designed for high power audio, disk head positioners and other linear applications.

- High Safe Operating Area (100% Tested) —
  2 A @ 80 V
- High DC Current Gain —
  h_{FE} = 15 (Min) @ I_C = 8 Adc

16 AMPERE
SILICON
POWER TRANSISTORS
200 AND 250 VOLTS
250 WATTS



CASE 1–07
TO–204AA
(TO–3)

MAXIMUM RATINGS

Rating	Symbol	MJ15023	MJ15025	Unit
Collector–Emitter Voltage	V_{CEO}	200	250	Vdc
Collector–Base Voltage	V_{CBO}	350	400	Vdc
Emitter–Base Voltage	V_{EBO}	5		Vdc
Collector–Emitter Voltage	V_{CEX}	400		Vdc
Collector Current — Continuous Peak (1)	I_C	16 30		Adc
Base Current — Continuous	I_B	5		Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	250 1.43		Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.70	°C/W

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 7

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) (I_C = 100 mAdc, I_B = 0)	MJ15023 MJ15025	$V_{CEO(sus)}$	 200 250	 — —	
Collector Cutoff Current (V_{CE} = 200 Vdc, $V_{BE(off)}$ = 1.5 Vdc) (V_{CE} = 250 Vdc, $V_{BE(off)}$ = 1.5 Vdc)	 MJ15023 MJ15025	I_{CEX}	 — —	 250 250	µAdc
Collector Cutoff Current (V_{CE} = 150 Vdc, I_B = 0) (V_{CE} = 200 Vdc, I_B = 0)	 MJ15023 MJ15025	I_{CEO}	 — —	 500 500	µAdc
Emitter Cutoff Current (V_{CE} = 5 Vdc, I_B = 0)	Both	I_{EBO}	—	500	µAdc
SECOND BREAKDOWN					
Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 50 Vdc, t = 0.5 s (non–repetitive)) (V_{CE} = 80 Vdc, t = 0.5 s (non–repetitive))		$I_{S/b}$	 5 2	 — —	Adc
ON CHARACTERISTICS					
DC Current Gain (I_C = 8 Adc, V_{CE} = 4 Vdc) (I_C = 16 Adc, V_{CE} = 4 Vdc)		h_{FE}	 15 5	 60 —	—
Collector–Emitter Saturation Voltage (I_C = 8 Adc, I_B = 0.8 Adc) (I_C = 16 Adc, I_B = 3.2 Adc)		$V_{CE(sat)}$	 —	 1.4 4.0	Vdc
Base–Emitter On Voltage (I_C = 8 Adc, V_{CE} = 4 Vdc)		$V_{BE(on)}$	—	2.2	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = 1 Adc, V_{CE} = 10 Vdc, f_{test} = 1 MHz)		f_T	4	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f_{test} = 1 MHz)		C_{ob}	—	600	pF

(1) Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤ 2%.

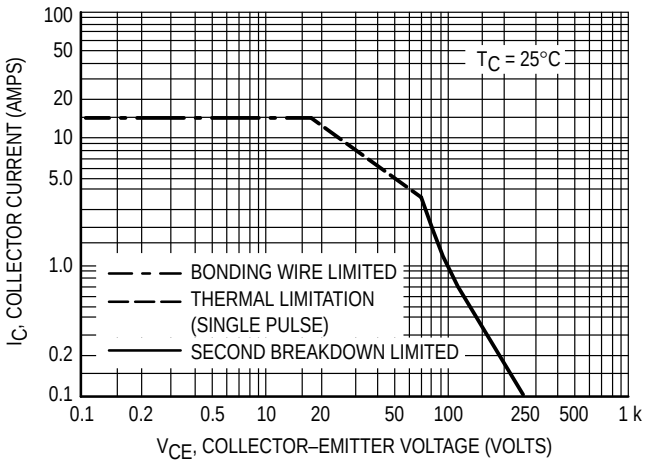

Figure 1. Active–Region Safe Operating Area

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)}$ = 200°C; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

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TYPICAL CHARACTERISTICS

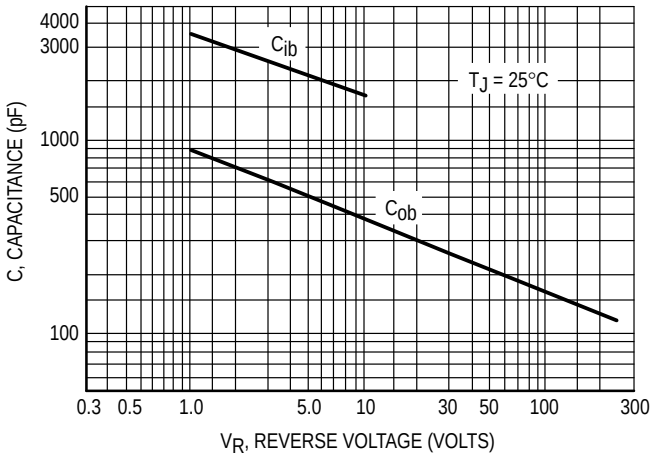

Figure 2. Capacitances

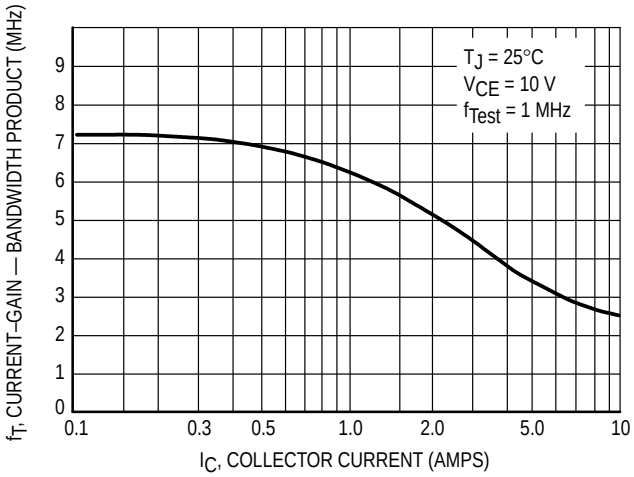

Figure 3. Current–Gain — Bandwidth Product

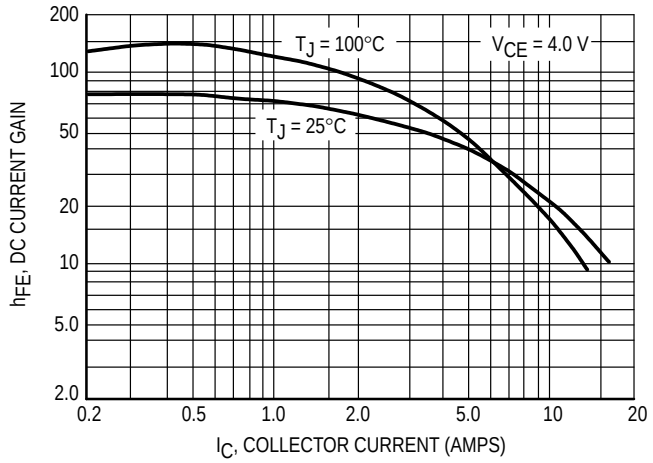

Figure 4. DC Current Gain

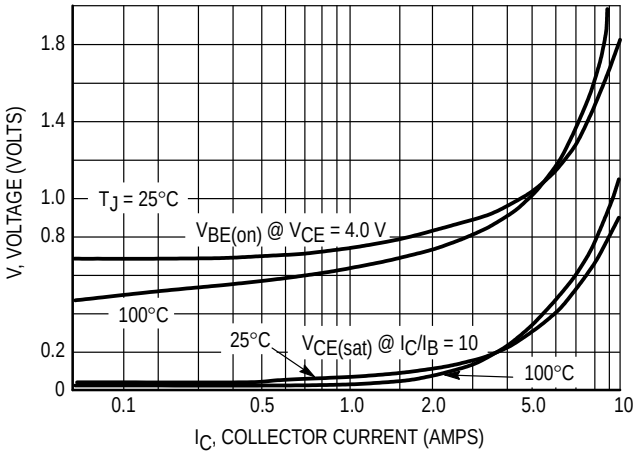

Figure 5. “On” Voltages

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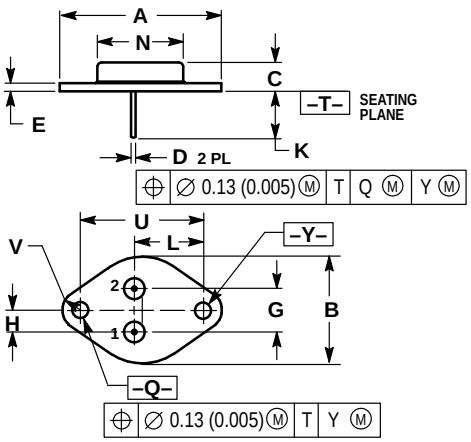
PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO–204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	—	1.050	—	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	—	0.830	—	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

CASE 1–07
TO–204AA (TO–3)
ISSUE Z

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